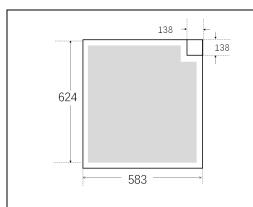


JMT2302AN

20V, 4A⁽¹⁾, N-channel MOSFET

Physical Characteristics

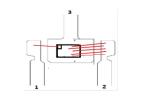


Die size: 624µm x 583µm (including scribe line)

Gate: 138µm x 138µm

Gross die / per 8" wafer =81500pcs

For SOT-23 package Suggest Bonding wire: Gate: 1*42um Cu Source: 5*42um Cu



Mechanical Data

| Nominal Back Metal Composition, Thickness: | Ti- Ni - Ag, (1kA°-2kA°-10kA°) | | |
|---|--------------------------------|--|--|
| Nominal Front Metal Composition, Thickness: | AICU(4um) | | |
| Wafer Diameter: | 200mm, with 010 notch | | |
| Wafer Thickness: | 160µm | | |
| Scribe line width | 60µm | | |
| Passivation | SiN | | |

Electrical Characteristics after SOT-23 package (T_J=25°C)

| Parameter | Description | Min. | Тур. | Max. | Unit | Test Condition |
|----------------------|-----------------------------------|------------------|------|------|------|---|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | 20 | _ | _ | V | V _{GS} =0V, I _D =250µA |
| Rds(on) | Static Drain-Source On-Resistance | _ | 23 | 30 | mΩ | V _{GS} =4.5V, I _D =4A ⁽¹⁾ |
| | | _ | 32 | 45 | mΩ | V _{GS} =2.5V, I _D =3A ⁽¹⁾ |
| V _{GS(th)} | Gate Threshold Voltage | 0.5 | 0.7 | 1 | V | V _{DS} = V _{GS} , I _D =250μA |
| IDSS | Drain-to-Source Leakage Current | _ | _ | 1 | μA | V _{DS} = 20V, V _{GS} = 0V |
| Igss | Gate-Body Leakage Current | _ | _ | ±100 | nA | V _{DS} = 0V, V _{GS} = ±12V |
| TJ, TSTG | Operating and Storage Temperature | -55℃ to 150℃ Max | | | | |

Note:

(1) This characteristics assumes the die are assembled in SOT-23 packages. Actual performance may degrade when assembled. JieJie does not guarantee device performance after assembly.



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